

16-Channel/Differential 8-Channel, CMOS High Speed Analog Multiplexer

The HI-516 is a monolithic, dielectrically isolated, high-speed, high-performance CMOS analog multiplexer. It offers unique built-in channel selection decoding plus an inhibit input for disabling all channels. The dual function of address input A₃ enables the HI-516 to be user programmed either as a single ended 16-Channel multiplexer by connecting 'out A' to 'out B' and using A₃ as a digital address input, or as an 8-Channel differential multiplexer by connecting A₃ to the V- supply. The substrate leakages and parasitic capacitances are reduced substantially by using the Intersil Dielectric Isolation process to achieve optimum performance in both high and low level signal applications. The low output leakage current (I_{D(OFF)} < 100pA at 25°C) and fast settling (t_{SETTLE} = 800ns to 0.01%) characteristics of the device make it an ideal choice for high speed data acquisition systems, precision instrumentation, and industrial process control.

For MIL-STD-883 compliant parts, request the HI-516/883 data sheet.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
HI3-0516-5	0 to 75	28 Ld PDIP	E28.6

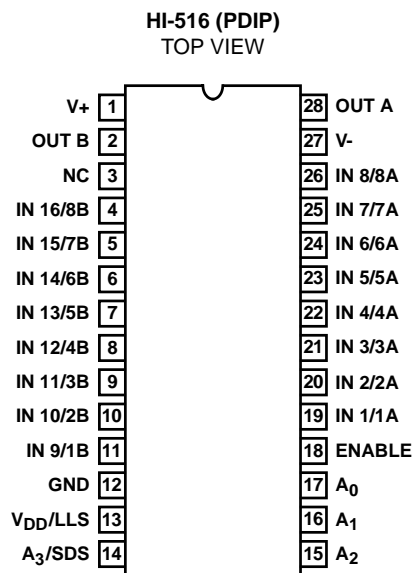
Features

- Access Time (Typical) 130ns
- Settling Time 250ns (0.1%)
- Low Leakage (Typical)
 - I_{S(OFF)} 10pA
 - I_{D(OFF)} 30pA
- Low Capacitance (Max)
 - C_{S(OFF)} 10pF
 - C_{D(OFF)} 25pF
- Off Isolation at 500kHz 55dB (Min)
- Low Charge Injection Error 20mV
- Single Ended to Differential Selectable (SDS)
- Logic Level Selectable (LLS)

Applications

- Data Acquisition Systems
- Precision Instrumentation
- Industrial Control

Pinout



Truth Tables

HI-516 USED AS A 16-CHANNEL MULTIPLEXER OR DUAL 8-CHANNEL MULTIPLEXER (NOTE 1)

USE A ₃ AS DIGITAL ADDRESS INPUT					ON CHANNEL TO	
ENABLE	A ₃	A ₂	A ₁	A ₀	OUT A	OUT B
L	X	X	X	X	None	None
H	L	L	L	L	1A	None
H	L	L	L	H	2A	None
H	L	L	H	L	3A	None
H	L	L	H	H	4A	None
H	L	H	L	L	5A	None
H	L	H	L	H	6A	None
H	L	H	H	L	7A	None
H	L	H	H	H	8A	None
H	H	L	L	L	None	1B
H	H	L	L	H	None	2B
H	H	L	H	L	None	3B
H	H	L	H	H	None	4B
H	H	H	L	L	None	5B
H	H	H	L	H	None	6B
H	H	H	H	L	None	7B
H	H	H	H	H	None	8B

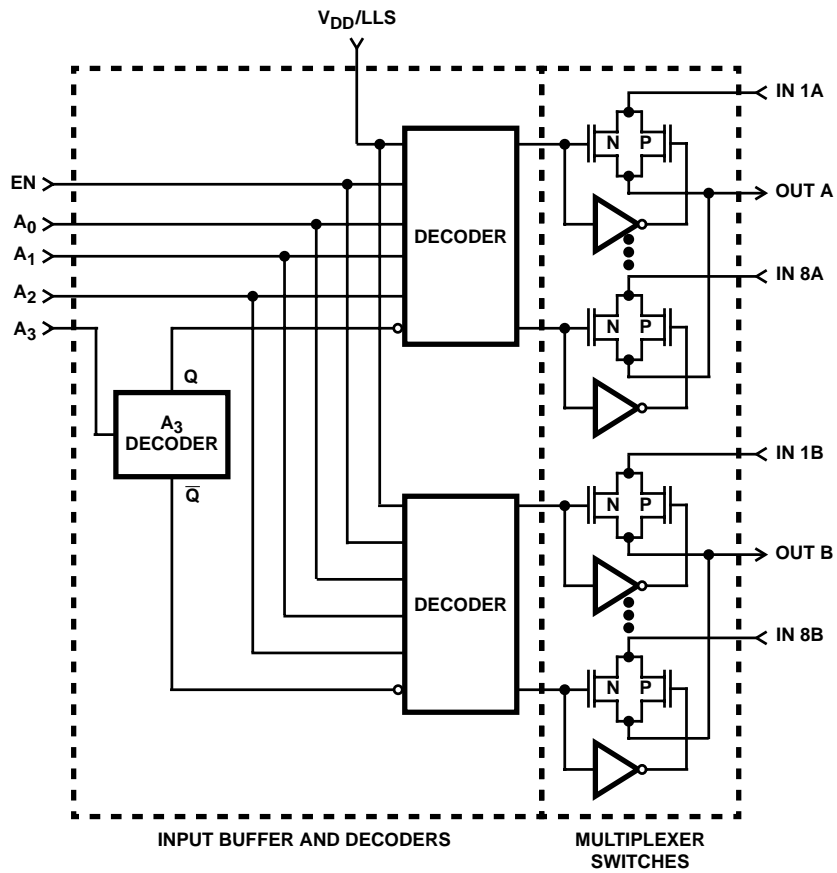
HI-516 USED AS A DIFFERENTIAL 8-CHANNEL MULTIPLEXER

A ₃ CONNECTED TO V- SUPPLY				ON CHANNEL TO	
ENABLE	A ₂	A ₁	A ₀	OUT A	OUT B
L	X	X	X	None	None
H	L	L	L	1A	1B
H	L	L	H	2A	2B
H	L	H	L	3A	3B
H	L	H	H	4A	4B
H	H	L	L	5A	5B
H	H	L	H	6A	6B
H	H	H	L	7A	7B
H	H	H	H	8A	8B

NOTE:

1. For 16-channel single-ended function, tie 'out A' to 'out B'; for dual 8-channel function use the A₃ address pin to select between MUX A and MUX B, where MUX A is selected with A₃ low.

Functional Block Diagram



A ₃ DECODE		
A ₃	Q	\bar{Q}
H	H	L
L	L	H
V-	L	L

HI-516

Electrical Specifications Supplies = +15V, -15V; V_{AH} (Logic Level High) = 2.4V, V_{AL} (Logic Level Low) = 0.8V; $V_{DD}/LLS = GND$. (Note 3) Unless Otherwise Specified **(Continued)**

PARAMETER	TEST CONDITIONS	TEMP (°C)	-5			UNITS
			MIN	TYP	MAX	
Input Leakage Current, I_{AL} (Low)		Full	-	-	25	μA
ANALOG CHANNEL CHARACTERISTICS						
Analog Signal Range, V_{IN}	Note 4	Full	-15	-	+15	V
On Resistance, r_{ON}	Note 5	25	-	620	750	Ω
		Full	-	-	1,000	Ω
Off Input Leakage Current, $I_{S(OFF)}$		25	-	0.01	-	nA
		Full	-	-	50	nA
Off Output Leakage Current, $I_{D(OFF)}$		25	-	0.03	-	nA
		Full	-	-	100	nA
On Channel Leakage Current, $I_{D(ON)}$		25	-	0.04	-	nA
POWER SUPPLY CHARACTERISTICS						
Power Dissipation, P_D		Full	-	-	900	mW
I_+ , Current	$V_{EN} = 2.4V$	Full	-	-	30	mA
I_- , Current		Full	-	-	30	mA

NOTES:

3. V_{DD}/LLS pin = open or grounded for TTL compatibility. V_{DD}/LLS pin = V_{DD} for CMOS compatibility.
4. At temperatures above 90°C, care must be taken to assure V_{IN} remains at least 1V below the V_{SUPPLY} for proper operation.
5. $V_{IN} = \pm 10V$, $I_{OUT} = -100\mu A$.
6. $V_{IN} = 0V$, $C_L = 100pF$, enable input pulse = 3V, $f = 500kHz$.
7. $V_{EN} = 0.8V$, $V_{IN} = 3V_{RMS}$, $f = 500kHz$, $C_L = 40pF$, $R_L = 1K$, Pin 3 grounded.

Test Circuits and Waveforms $V_{DD}/LLS = GND$, Unless Otherwise Specified.

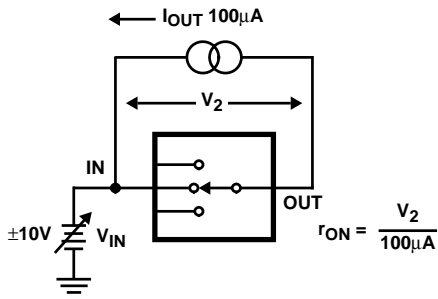


FIGURE 1. ON RESISTANCE TEST CIRCUIT

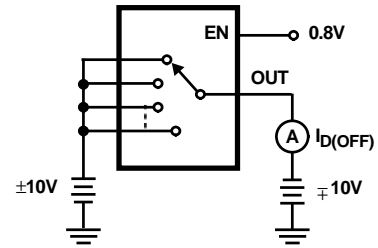


FIGURE 2. $I_{D(OFF)}$ TEST CIRCUIT (NOTE 8)

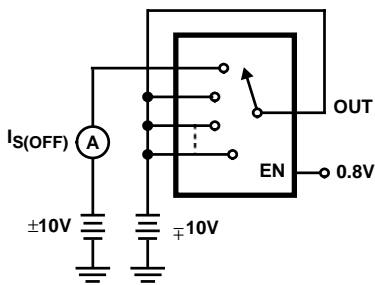


FIGURE 3. $I_{S(OFF)}$ TEST CIRCUIT (NOTE 8)

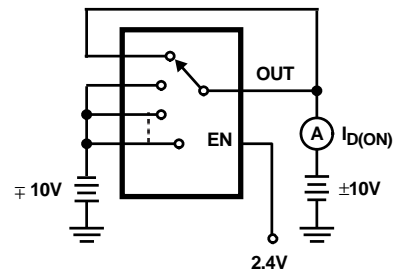


FIGURE 4. $I_{D(ON)}$ TEST CIRCUIT (NOTE 8)

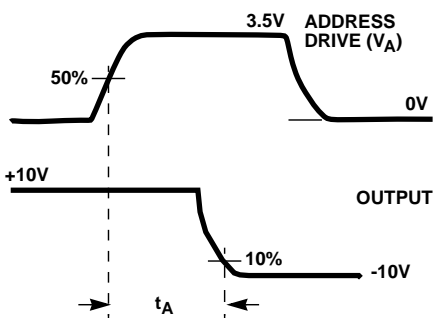


FIGURE 5A. MEASUREMENT POINTS

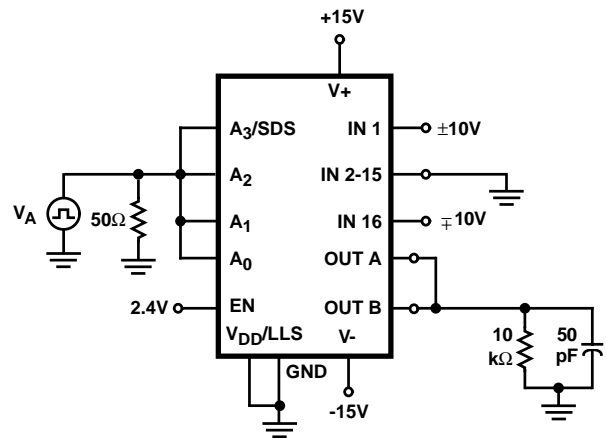


FIGURE 5B. TEST CIRCUIT

NOTE:

8. Two measurements per channel: $\pm 10V$ and $\mp 10V$. (Two measurements per device for $I_{D(OFF)}$ $\pm 10V$ and $\mp 10V$).

FIGURE 6. ACCESS TIME

Test Circuits and Waveforms $V_{DD}/LLS = GND$, Unless Otherwise Specified. (Continued)

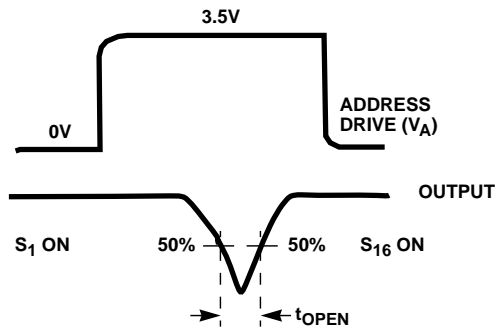


FIGURE 7A. MEASUREMENT POINTS

FIGURE 7. BREAK-BEFORE-MAKE DELAY

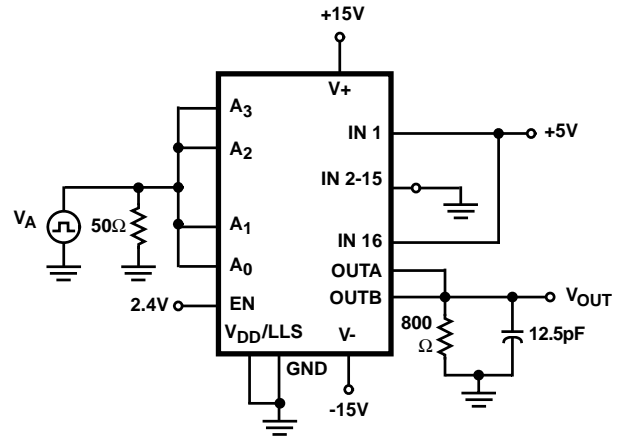


FIGURE 7B. TEST CIRCUIT

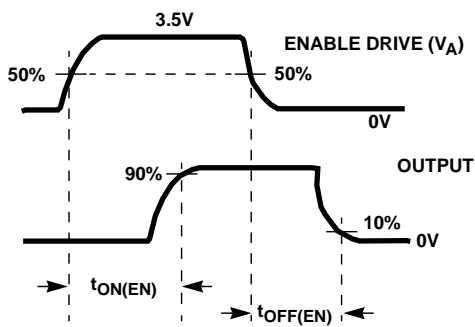


FIGURE 8A. MEASUREMENT POINTS

FIGURE 8. ENABLE DELAYS

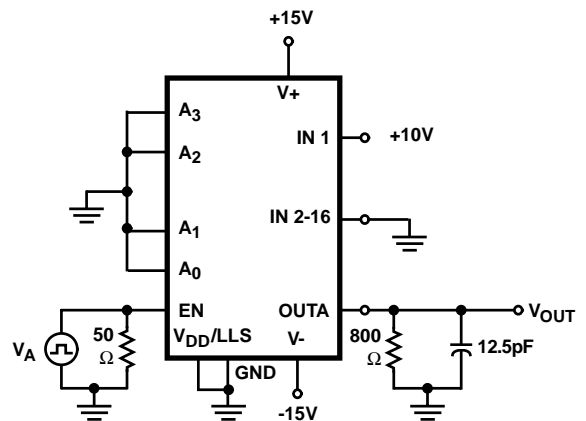


FIGURE 8B. TEST CIRCUIT

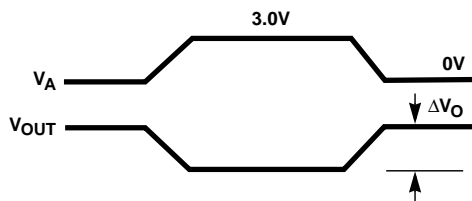


FIGURE 9A. MEASUREMENT POINTS

FIGURE 9. CHARGE INJECTION

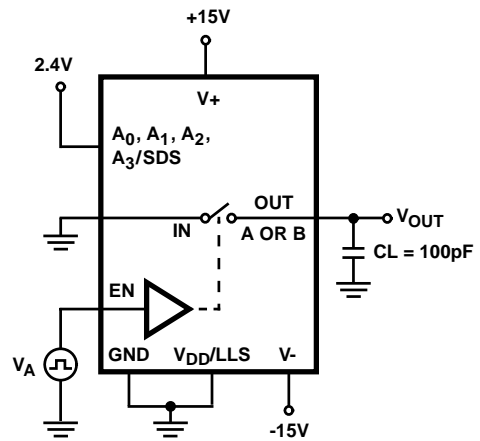


FIGURE 9B. TEST CIRCUIT

ΔV_O is the measured voltage error due to charge injection. The error in coulombs is $Q = C_L \times \Delta V_O$.

Die Characteristics

DIE DIMENSIONS:

2250μm x 3720μm x 485μm

METALLIZATION:

Type: CuAl
 Thickness: 16kÅ ±2kÅ

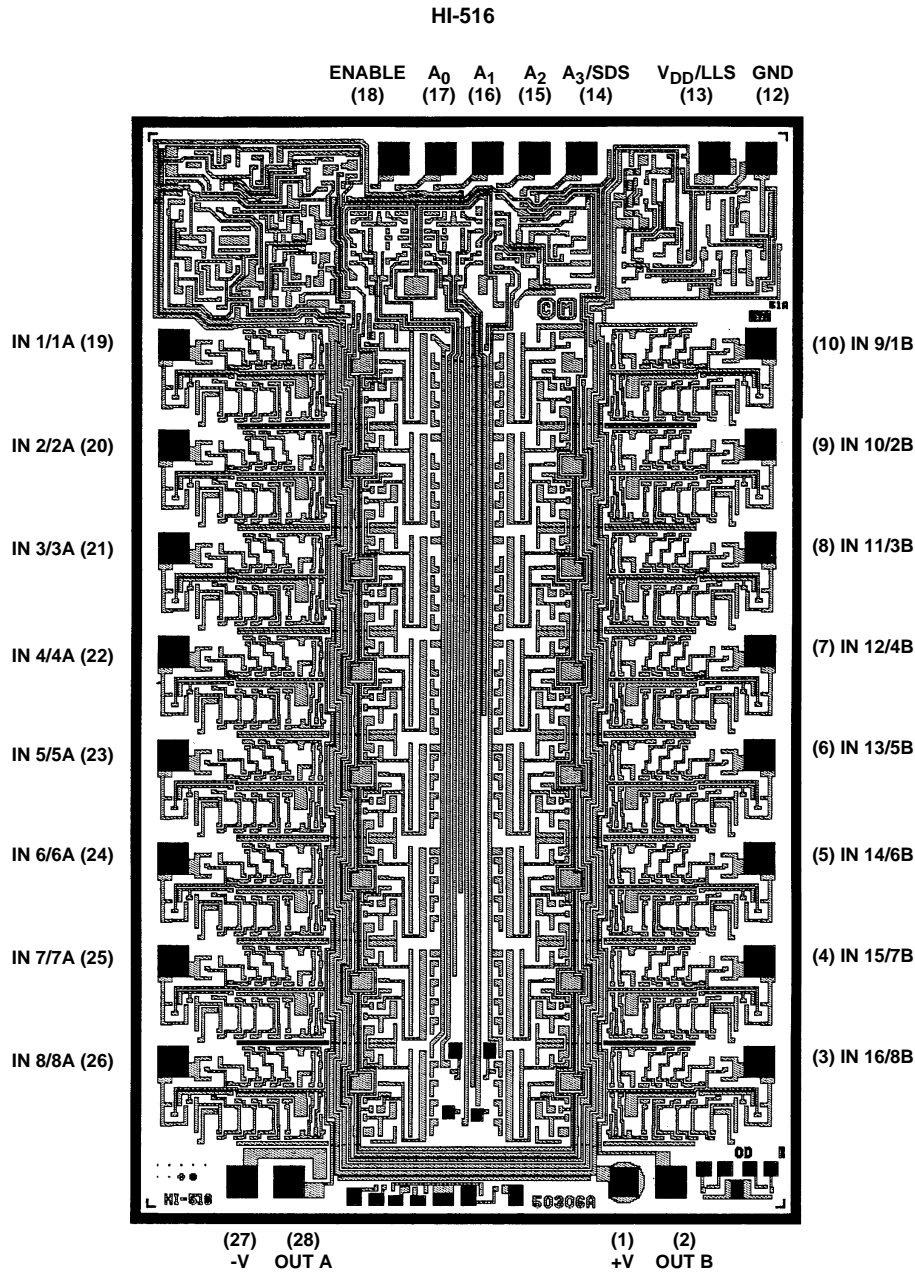
PASSIVATION:

Type: Nitride Over Silox
 Nitride Thickness: 3.5kÅ ±1kÅ
 Silox Thickness: 12kÅ ±2kÅ

WORST CASE CURRENT DENSITY:

1.64 x 10⁵ A/cm²

Metallization Mask Layout



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